



#10/A
11/22/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:
OHMI *et al.*

Application No.: 09/866,576

Filed: May 29, 2001

Title: SEMICONDUCTOR DEVICE FORMED ON (111)
SURFACE OF A Si CRYSTAL AND FABRICATION PROCESS
THEREOF

Confirmation No. 4482

ART UNIT: 2811

Examiner: OWENS, D.

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November 14, 2002

AMENDMENT

Hon. Commissioner of Patents
Washington, DC 20231

Sir:

Responsive to the Office Action dated August 14, 2002, please amend the above
identified application as follows:

IN THE CLAIMS

Please amend claims 1 and 7 as follows:

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B1
A
-
1. (Amended) A semiconductor device comprising:
a Si crystal having a (111) surface; and
an insulation film formed on said (111) surface of said Si crystal,
wherein at least a part of said insulation film comprises a Si oxide film containing Kr.
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7. (Amended) A Semiconductor device as claimed in claim 1,
wherein said crystal surface forms a principal surface of said Si crystal.
-
- A2

See the attached Appendix for the changes made to effect the above claims.